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# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T <sub>b</sub> =25°C)					電気的特性 (T <sub>b</sub> =25°C)										外形	備考
				V <sub>ceo</sub> (V)	V <sub>ceo</sub> (V)	I <sub>c</sub> (mA)	P <sub>c</sub> (mW)	T <sub>j</sub> (°C)	I <sub>ceo</sub> 最大値 (μA)	直流又はパルスI <sub>BE</sub>		バイアス		h <sub>FE</sub>	h <sub>FE</sub> h <sub>FE</sub> * (Ω)	h <sub>FE</sub> h <sub>FE</sub> * (×10 <sup>-4</sup> )	h <sub>FE</sub> h <sub>FE</sub> * (μS)	f <sub>αB</sub> f <sub>r</sub> * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I<sub>CBO</sub> MAXIMUM VALUE AND V<sub>CB</sub> VALUE (CRITERIA FOR MEASURING I<sub>CBO</sub>)
- 7 STANDARD VALUE OF DC/PULSE h<sub>FE</sub> AND V<sub>CE</sub>, I<sub>C</sub> (CRITERIA FOR MEASURING DC/PULSE h<sub>FE</sub>)
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V<sub>CB</sub>, I<sub>E</sub> (CRITERIA FOR MEASURING h PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f<sub>αB</sub> OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF f<sub>r</sub>.
- 10 C<sub>ob</sub> AND r<sub>bb'</sub> OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN r<sub>bb'</sub> COLUMN WHICH INDICATES VALUE OF h<sub>ie</sub> (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 (T <sub>a</sub> = 25°C)					電 気 的 特 性 (T <sub>a</sub> = 25°C)										外形	備考							
				V <sub>CEO</sub> (V)	V <sub>EMO</sub> (V)	I <sub>C</sub> (mA)	P <sub>C</sub> (mW)	T <sub>J</sub> (°C)	I <sub>CMO</sub> 最大値		直流又はパルス hFE		バイアス		h <sub>FE</sub> *	h <sub>FE</sub> *	h <sub>FE</sub> *	h <sub>FE</sub> *			f <sub>β</sub> f <sub>T</sub> *	C <sub>ob</sub> (pF)	r <sub>bb</sub> h <sub>ibreal</sub> *				
									μA	V <sub>CE</sub> (V)	V <sub>CE</sub> (V)	I <sub>C</sub> (mA)	V <sub>CE</sub> (V)	I <sub>E</sub> (mA)													
2SA773	ソニー	RF. PA	Si. EP	-60	-6	-1A	750	120	-0.2	-25	250	-2	-100	-2	10					65*	25	259	2SC1475 とコンブリ				
* 774	松下	RF. LN	Si. EP	-35	-5	-50	150	175	-0.1	-10	540	-5	-2	-5	2					3500	3	60	120*	5	100	243	
* 775	日立	PA	Si. T	-100	-4	-700	12.5W (T <sub>c</sub> =25°C)	150	-10		90	-4	-50	-4	30								30*	35	25	268	
* 776	東芝	RF. LN	Si. EP	-55	-5	-50	200	150	-0.1	-30	300	-6	-2	-6	1	285	7300	1	21			180*	3	35	195		
* 777	松下	PA	"	-80	-5	-500	750	135	-0.1	-20	160	-10	150	-10	50							120*	20	2k*	165	2SC1509 とコンブリ	
* 778	日立	SW	Si. T	-150	-5	-50	200	125	-1	-100	100	-3	-15	-3	15							50*	<4		138		
* 779	"	RF. PA. SW	Si. E	-35	-5	-1.5A	10W (T <sub>c</sub> =25°C)	150	-20	-30	60-200	-2	-500	-2	200	t <sub>on</sub> =130nS, t <sub>off</sub> =550nS						110*	50		234		
* 780	"	PA. SW	"	-50	-4	-1A	10W (T <sub>c</sub> =25°C)	150	-1	-30	120	-4	-50	-4	50							120*	8		234	2SC1517 とコンブリ	
* 781	"	SW. RF	"	-20	-4	-200	200	125	-0.2	-16	20-200	-0.5	-30	-1	30	t <sub>on</sub> <70nS, t <sub>off</sub> <120nS						550*	25		138		
* 782	東洋電具	RF. Conv. Mix Osc. PA. AF	"	-80	-5	-30	150	125	-1	-50	150	-6	-1	-6	1					7.1k	0.4	6.7	200*	3	C <sub>e</sub> r <sub>bb</sub> 160pS	235	
* 783	"	"	"	-50	-5	-30	150	125	-1	-30	150	-6	-1	-6	1					7.1k	0.4	6.7	200*	3	C <sub>e</sub> r <sub>bb</sub> 160pS	235	
* 784	"	"	"	-25	-5	-30	150	125	-1	-15	130	-6	-1	-6	1					7.1k	0.4	6.7	200*	3	C <sub>e</sub> r <sub>bb</sub> 160pS	235	
* 785	"	"	"	-80	-5	-50	150	125	-1	-50	150	-3	-10	-5	1					6.7k	0.8	10	180*	6.5	C <sub>e</sub> r <sub>bb</sub> 150pS	235	
* 786	"	"	"	-50	-5	-50	150	125	-1	-30	150	-3	-10	-5	1					6.7k	0.8	10	180*	6.5	C <sub>e</sub> r <sub>bb</sub> 150pS	235	
* 787	"	"	"	-20	-5	-50	150	125	-1	-15	150	-3	-10	-6	1					6.7k	0.8	10	180*	6.5	C <sub>e</sub> r <sub>bb</sub> 150pS	235	
* 788	"	RF. Conv. Mix Osc. PA. AF. LN	"	-50	-5	-30	150	125	-1	-30	150	-3	-10	-6	1	NF=2dB (f=1kHz) 7.1k						200*	3	C <sub>e</sub> r <sub>bb</sub> 160pS	235		
* 789	"	"	"	-25	-5	-30	150	125	-1	-15	150	-3	-10	-6	1	NF=2dB (f=1kHz) 7.1k						200*	3	C <sub>e</sub> r <sub>bb</sub> 160pS	235		
* 790	"	RF. Conv. Mix Osc. PA	"	-40	-6	-300	300	125	-1	-24	10,000	-5	-100	-5	10							200*	3	C <sub>e</sub> r <sub>bb</sub> 100pS	235		
* 791	"	"	"	-25	-6	-300	300	125	-1	-15	10,000	-5	-100	-5	10							200*	3	C <sub>e</sub> r <sub>bb</sub> 100pS	235		
* 792																											
* 793																											
* 794	松下	PA	Si. EP	-100	-5	-500	1.2W	150	-1	-100	160	-10	-150	-10	50							120*	20	3.5k*	222	2SC1567 とコンブリ	
* 795	"	"	"	-150	-5	-250	10W (T <sub>c</sub> =80°C)	150	-30	-60	120	-10	-100	-10	50							120*	15	15	236	2SC1565 とコンブリ	
* 796	新日無	SW	"	-30	-10	-300	300	125	-1	-20	40,000	-6	-100			t <sub>on</sub> <600nS, t <sub>off</sub> <1.2μS									138	2SC1432 とコンブリ	
* 797																											
* 798	三菱	Diff. LN	Si. EP	-50	-5	-100	200 unit	125	-0.1	-35	250- 1200	-6	1	-6	1	ΔV <sub>BE</sub> <10mV hFE <sup>小</sup> /hFE <sup>大</sup> =0.8-1.0						100*	3.0		274A	2素子複合	
* 799	富士通	SW	"	-60	-5	-1.5A	1W	200	-0.5	-50	54	-1	-500			t <sub>on</sub> <45nS, t <sub>off</sub> <110nS t <sub>arr</sub> <80nS									84C		
* 800	日電	RF	Si. E	-20	-3	-30	250	200	-0.1	-15	60	-10	-10	-10	10	S <sub>21</sub>   <sup>2</sup> >5dB (10V, 10mA, 1GHz)						2500*	0.9		50C		
* 801	"	"	"	-20	-3	-50	300	200	-0.1	-10	90	-10	-15	-5	15	S <sub>21</sub>   <sup>2</sup> =10dB (10V, 20mA, 1GHz)						4000*	1.2		130		
* 802	東洋電具	SW	Si. TP	-130	-5	-30	150	125	-1	-80	56-270	-3	-5	-5	2							50*	8		235		